

FEATURES

- . Low power loss, high efficient
- . High surge current capability
- . Low forward voltage drop
- . For use in low voltage, high frequency inverters, free wheeling application
- . Guarding for overvoltage protection
- . Metal silicon junction, majority carrier conduction

. High temperature soldering guaranteed:
 250°C/10 seconds/.375", (9.5mm) lead lengths

MECHANICAL DATA

Case: Molded plastic use UL94V-0 recognized flame retardant epoxy

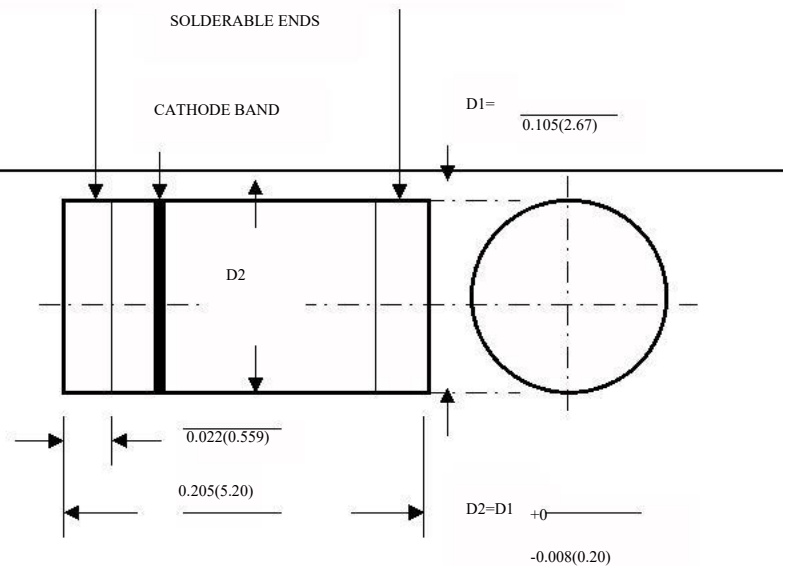
Terminals: Plated terminals, solderable per MIL-STD-202, method 208

Polarity: Blue color band on body denotes cathode

Mounting position: Any

Weight: 0.12 grams

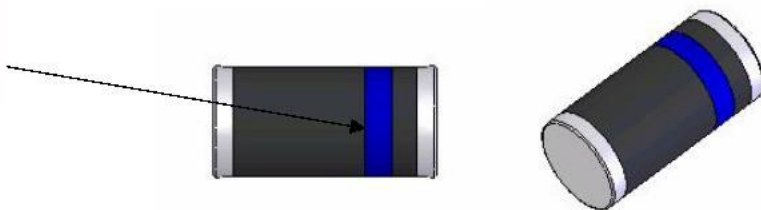
DO-213AB / MELF



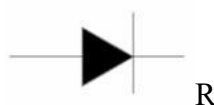
Dimension in inches (millimeters)

DEVICEMARKING

陰極線



整流二極管通用符號:



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C Ambient temp. Unless otherwise specified.

Single phase, half sine wave, 60HZ, resistive or inductive load.

For capacitive load, derate current by 20%

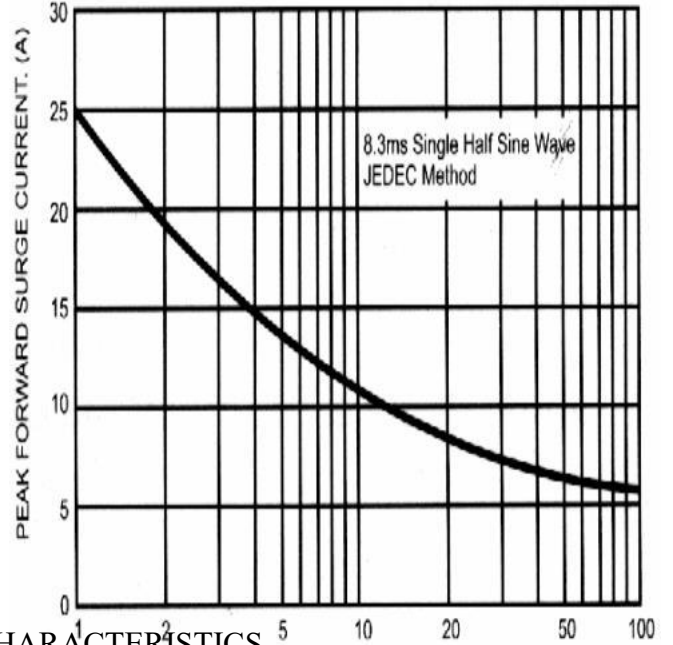
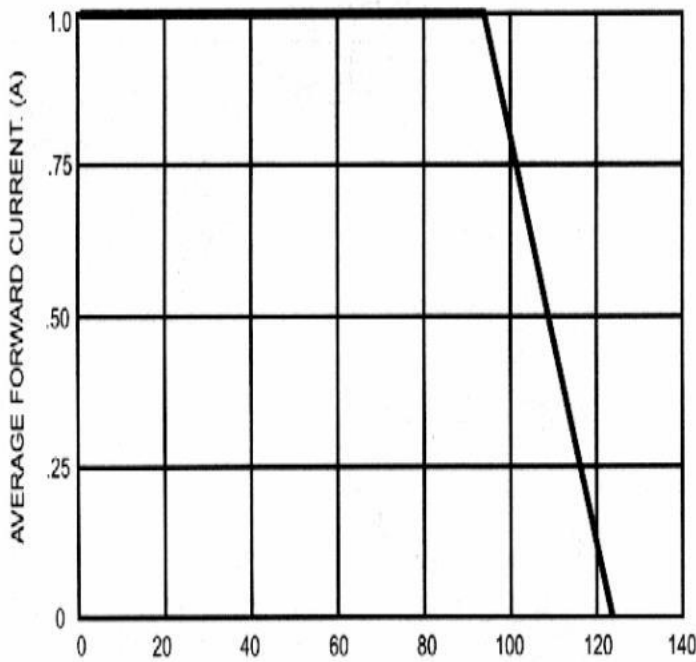
	SYMBOL	SM5817	SM5818	SM5819	UNITS
Maximum Current Peak Reverse	VRRM	20	30	40	Volts
Maximum RMS Voltage	VRMS	14	24	28	Volts
Maximum DC Blocking Voltage	VDC	20	30	40	Volts
Maximum Average Forward Rectified Current	I(AV)	1.0			Amps
Peak Forward Surge Current Single Sine-wave on Rated Load (JEDEC Method)	IFSM	25.0			Amps
Maximum Instantaneous Forward Voltage Drop at 1.0A DC	VF	0.45	0.55	0.6	Volts
Maximum DC Reverse Current T =25°C	IR	1.0			mA
		10.0			
Typical Thermal Resistance	R θ JA	15			°C/W
Typical Junction Capacitance	CJ	110.0		80.0	pF
Operating Junction Temperature	TJ	-55 to +125		-55 to +150	°C
Storage Temperature Range	TSTG	-55 to +150			°C

Notes: 1. Thermal Resistance Junction Ambient

2. Measured at 1 MHz and Applied Reverse Voltage of 4.0 V D.C.

SM5817 THRU SM5819
SURFACE MOUNT SCHOTTKY RECTIFIERS

RATING AND CHARACTERISTIC CURVES SM5817 THRU SM5819



CHARACTERISTICS

